



TIGER ELECTRONIC CO.,LTD

TO-92 Plastic-Encapsulate Transistors

BC556/BC557/BC558 TRANSISTOR (PNP)

FEATURES

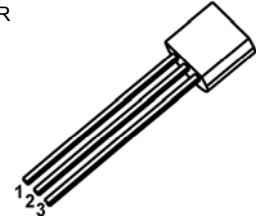
- High Voltage
- Complement to BC546/BC547/BC548

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	BC556 -80	V
		BC557 -50	
		BC558 -30	
V _{CEO}	Collector-Emitter Voltage	-65	V
		-45	
		-30	
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-100	mA
P _C	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-92

1. COLLECTOR
2. BASE
3. EMITTER



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BC556 BC557 BC558	V _{CBO} I _C = -100μA, I _E =0	-80 -50 -30			V
Collector-emitter breakdown voltage	BC556 BC557 BC558	V _{CEO} I _C = -2mA, I _B =0	-65 -45 -30			V
Emitter-base breakdown voltage	V _{EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	BC556 BC557 BC558	I _{CBO} V _{CB} = -70 V, I _E =0 V _{CB} = -45 V, I _E =0 V _{CB} = -25V, I _E =0			-0.1	μA
Collector cut-off current	BC556 BC557 BC558	I _{CEO} V _{CE} = -60 V, I _B =0 V _{CE} = -40 V, I _B =0 V _{CE} = -25 V, I _B =0			-0.1	μA
Emitter cut-off current	BC556 BC557 BC558	I _{EBO} V _{EB} = -5 V, I _C =0			-0.1	μA
DC current gain	BC556 BC557 BC558 BC557A BC556B/BC557B/BC558B BC557C	h _{FE} V _{CE} =-5V, I _C = -2mA	120 120 120 120 180 420		800 800 800 220 460 800	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA, I _B = -5mA			-0.65	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100mA, I _B =-5mA			-1	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA f = 100MHz	150			MHz